Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently amended) A method of forming a ferroelectric ~~substance~~ thin film, comprising:

forming a seed layer ~~including~~ containing an ultra-fine particle powder ~~containing~~ comprised of an element constituting [[a]] the ferroelectric ~~substance~~ thin film to be subsequently formed on a surface of a substrate; and

forming the ferroelectric ~~substance~~ thin film on the seed layer.

2. (Currently amended) The method of forming a ferroelectric ~~substance~~ thin film as claimed in claim 1, wherein forming the seed layer includes:

applying a solution containing [[an]] the element constituting the ferroelectric ~~substance~~ thin film to the surface of the substrate; and

drying and baking the solution applied to the substrate.

3. (Currently amended) The method of forming a ferroelectric ~~substance~~ thin film according to claim 2, wherein forming the ferroelectric ~~substance~~ thin film includes annealing the seed layer for crystallization.

4-5. (canceled)

6. (Currently amended) A method of forming a ferroelectric ~~substance~~ memory including an FET of an MFMIS structure, said method comprising:

forming a gate insulating film on a semiconductor substrate and between source-drain regions;

forming a floating gate on the gate insulating film;

forming a ferroelectric ~~substance~~ layer on the floating gate; and

forming a control gate on the ferroelectric ~~substance~~ layer,

wherein forming the ferroelectric ~~substance~~ layer comprises:

forming a seed layer ~~including an ultra-fine particle powder containing~~ on a surface of the floating gate, the seed layer containing an ultra-fine particle powder comprised of an element constituting a ferroelectric ~~substance~~ thin film to be subsequently formed on the seed layer; and

forming the ferroelectric ~~substance~~ thin film on the seed layer.

7-8. (canceled)

9. (Currently amended) A method of forming a ferroelectric ~~substance~~ memory comprising:

forming an FET including a gate electrode formed on a surface of a semiconductor substrate between source-drain regions, the source-drain regions formed on [[a]] the surface of the semiconductor substrate through a gate insulating film; and

forming a ferroelectric ~~substance~~ capacitor connected with one of the source-drain regions of the FET through a storage node contact,

wherein forming the ferroelectric ~~substance~~ capacitor comprises:

forming a first electrode;

forming a seed layer ~~including ultra-fine particle powder containing an element constituting a ferroelectric substance thin film~~ on a surface of the first electrode, the seed layer containing an ultra-fine particle powder comprised of an element constituting a feeoelectric thin film to be subsequently formed on the seed layer; and

forming the ferroelectric ~~substance~~ thin film on the seed layer.